

2006
IEEE
International
Reliability
Physics
Symposium
Proceedings

44th Annual

San Jose, California • March 26–30, 2006

Sponsored by
the IEEE Electron Devices Society and
the IEEE Reliability Society

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IEEE Catalog No. 06CH37728
ISBN: 0-7803-9498-4 Softbound Edition
Library of Congress Number: 82-640313

PREFACE

by Carole Graas, 2006 IRPS General Chair

It is truly my pleasure to present the 44th edition of the IRPS proceedings for your reference. The technical information contained in this volume is the culmination of the efforts of many people, most notably the authors whose work has been selected for publication and is described in detail in the pages that follow. This year again, we had a record number of submissions, from which a record number of papers were selected. The papers in this volume and their presentation at the Symposium represent the core focus of the IRPS.

These proceedings also represent the efforts of many IRPS technical and management committee members who volunteer their skills, time, and energy, along with help from our experienced consultants. Together, they continue to make the IRPS the leading forum for publishing, presenting, and discussing recent advances in the broad area of microelectronics reliability. To the authors, volunteers, and consultants, I give my thanks for helping make the IRPS an annual success and an essential venue serving the worldwide microelectronics reliability community.

It is also my pleasure to introduce our keynote speaker, Tim Collopy, from IBM's System and Technology Group. Every year the keynote address is a much anticipated event, meant to contribute a broad and forward-looking view of our field. Tim's presentation, titled "Adaptation of Reliability Methodologies to Market Expectations

and Technology Roadmaps" will discuss chip qualification strategies and their contributions to clients' success.

Rich Blish and Bob Thomas' special paper titled "Jewel Recovery from Past IRPS Proceedings" will take you on a journey through the past 43 symposiums, where they will act as tour guides to some of the most 'relevant and interesting papers' in microelectronics reliability. And they will surprise you with a very ingenious product of their work...

Likewise, I invite you to another journey through time at the Computer History Museum, where the fascinating past will meet the exciting present, with more state-of-the-art presentations by our poster authors. Our poster session is an important element of our technical program, and poster summaries are included in these proceedings.

I hope that once again, these proceedings, together with the companion color CDROM, become a valuable piece of your reference library for a long time to come. A virtual IRPS 2006 on DVD-ROMs will be available soon after the Symposium (check www.irps.org for availability) that contains video, audio, and presentation material for all of the technical presentations. The entire IRPS team hopes that you enjoy this symposium and will continue to join us and contribute to future meetings.

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